

Features:

- Isolated mounting base 3000V~
- Pressure contact technology with
Increased power cycling capability
- Space and weight saving

Typical Applications

- Various rectifiers
- DC supply for PWM inverter

V_{RSM}	V_{RRM}	品名
900V	800V	Mx1000D80C
1100V	1000V	Mx1000D100C
1300V	1200V	Mx1000D120C
1500V	1400V	Mx1000D140C
1700V	1600V	Mx1000D160C
1900V	1800V	Mx1000D180C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_j(^{\circ}\text{C})$	VALUE			UNIT
				Min.	Typ.	Max.	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Single side cooled, $T_c=100^{\circ}\text{C}$	150			1000	A
$I_{F(RMS)}$	RMS forward current		150			1570	A
I_{RRM}	Repetitive peak current	at V_{RRM}	150			50	mA
I_{FSM}	Surge forward current	10ms half sine wave $V_R=0.6V_{RRM}$	150			28	kA
I^2t	I^2t for fusing coordination					3920	$\text{A}^2\text{s}\cdot 10^3$
V_{FO}	Threshold voltage		150			0.70	V
r_F	Forward slope resistance					0.138	m Ω
V_{FM}	Peak forward voltage	$I_{FM}=3000\text{A}$	25			1.44	V
$R_{th(j-c)}$	Thermal resistance Junction to case	D.C. Single side cooled per chip				0.048	$^{\circ}\text{C}/\text{W}$
$R_{th(c-h)}$	Thermal resistance case to heatsink	D.C. Single side cooled per chip				0.020	$^{\circ}\text{C}/\text{W}$
V_{iso}	Isolation voltage	50Hz, R.M.S, $t=1\text{min}$, $I_{iso}:1\text{mA}(\text{max})$		3000			V
F_m	Terminal connection torque(M12)			12.0		16.0	N·m
	Mounting torque(M8)			10.0		12.0	N·m
T_{vj}	Junction temperature			-40		150	$^{\circ}\text{C}$
T_{stg}	Stored temperature			-40		125	$^{\circ}\text{C}$
W_t	Weight				3660		g
Outline	M08						

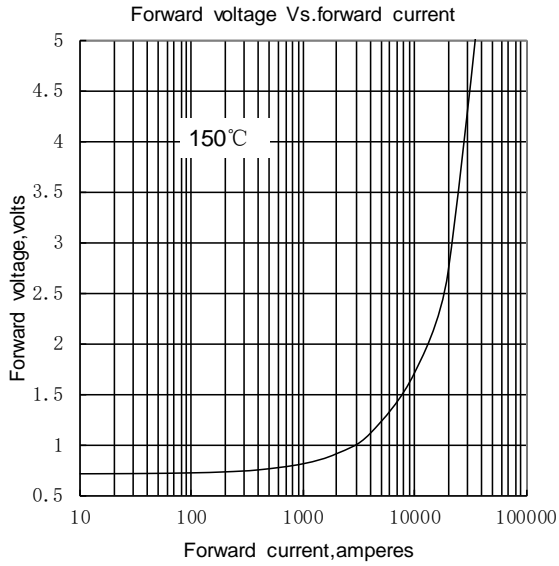


Fig.1

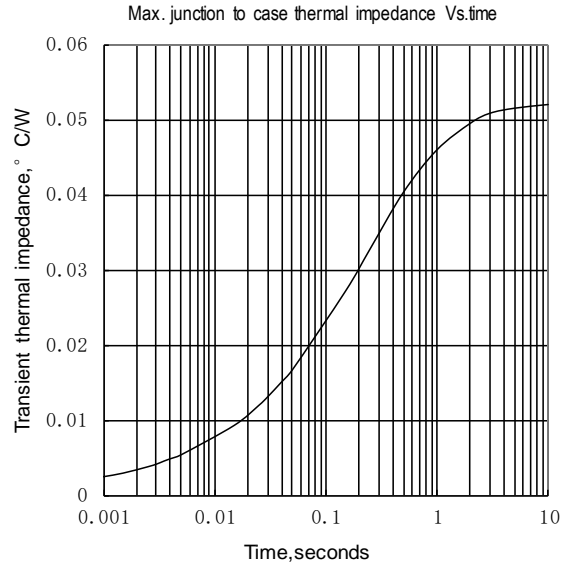


Fig.2

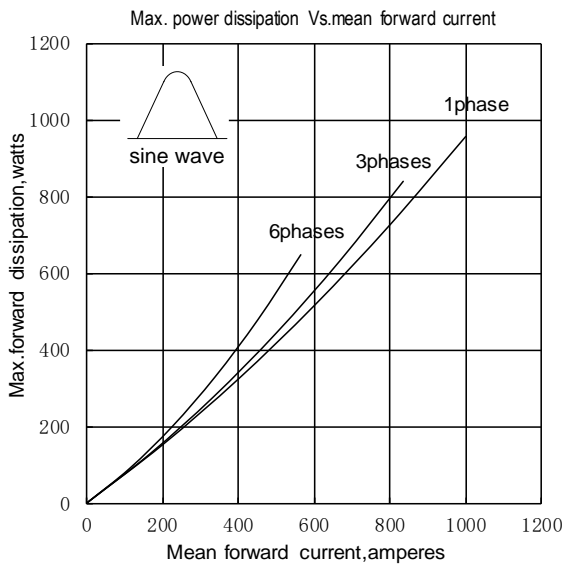


Fig.3

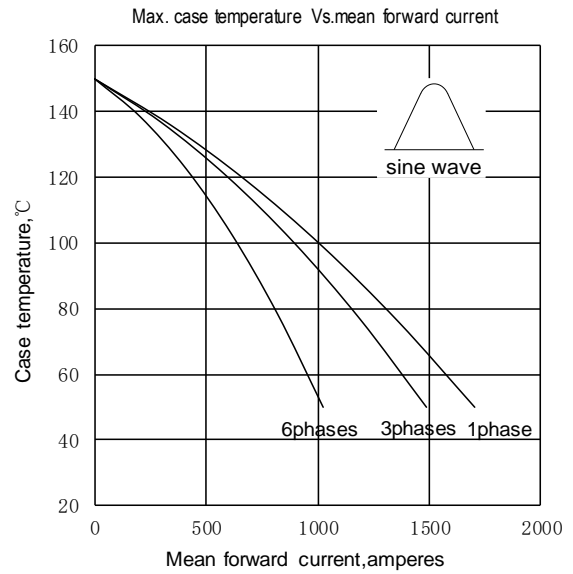


Fig.4

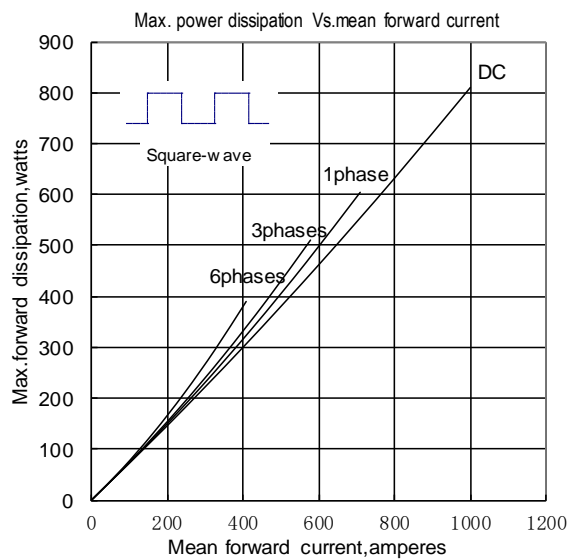


Fig.5

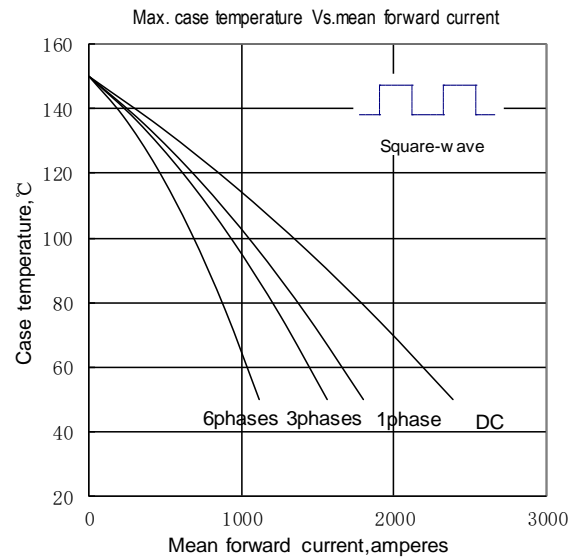


Fig.6

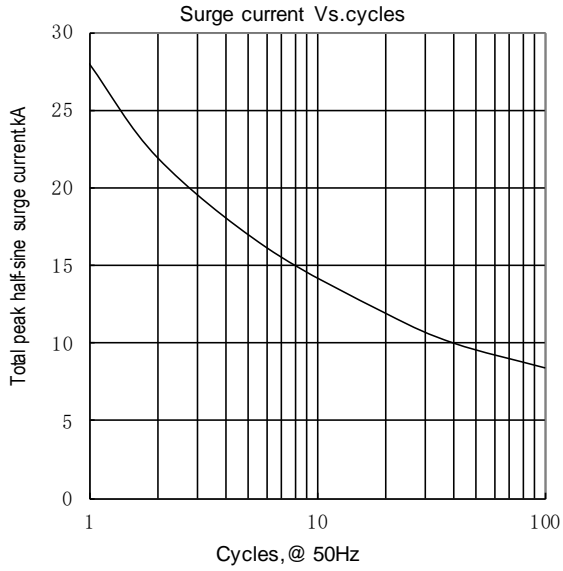
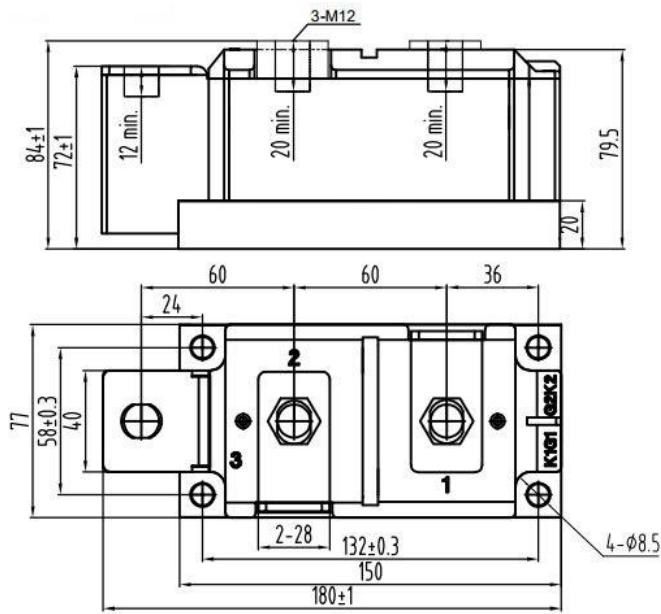
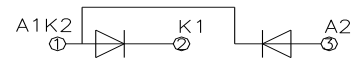


Fig.7

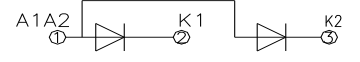


Unmarked dimensional tolerance : ±0.5mm

MD1000D**C



MR1000D**C



MC1000D**C

